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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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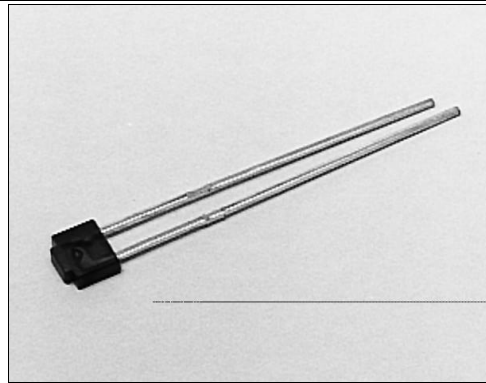


SEP8507

GaAs Infrared Emitting Diode

FEATURES

- End-emitting plastic package
- 135° (nominal) beam angle
- 935 nm wavelength
- Low profile for design flexibility
- Mechanically and spectrally matched to SDP8407 phototransistor



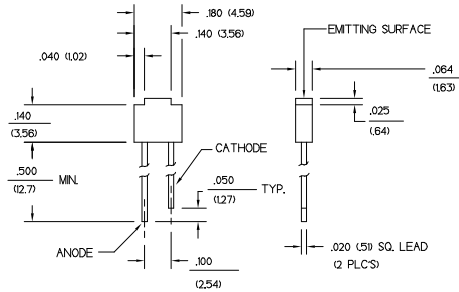
INFRA-18.TIF

DESCRIPTION

The SEP8507 is a gallium arsenide infrared emitting diode molded in an end-emitting red plastic package. The chip is positioned to emit radiation from the top of the package. Lead lengths are staggered to provide a simple method of polarity identification.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals ±0.008(0.20)
2 plc decimals ±0.020(0.51)



DIM_009.cdr

SEP8507

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ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Total Power Output SEP8507-001	P_o	0.40			mW	$I_F=20$ mA
Forward Voltage	V_F		1.5		V	$I_F=20$ mA
Reverse Breakdown Voltage	V_{BR}	3.0			V	$I_R=10$ μ A
Peak Output Wavelength	λ_p		935		nm	
Spectral Bandwidth	$\Delta\lambda$		50		nm	
Spectral Shift With Temperature	$\Delta\lambda_p/\Delta T$		0.3		nm/°C	
Beam Angle ⁽¹⁾	\emptyset		135		degr.	$I_F=$ Constant
Radiation Rise And Fall Time	t_r, t_f		0.7		μ s	

Notes

1. Beam angle is defined as the total included angle between the half intensity points.

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Continuous Forward Current	60 mA
Power Dissipation	100 mW ⁽¹⁾
Operating Temperature Range	-40°C to 85°C
Storage Temperature Range	-40°C to 85°C
Soldering Temperature (5 sec)	240°C

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 0.66 mW/°C.

SCHEMATIC



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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SEP8507

GaAs Infrared Emitting Diode

Fig. 1 Radiant Intensity vs Angular Displacement gra_032.ds4

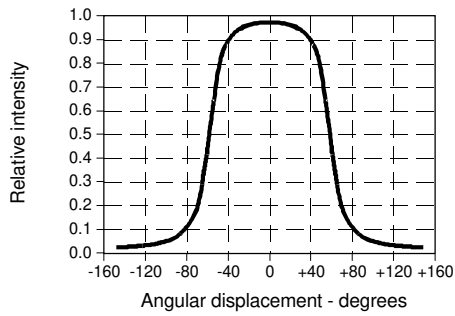


Fig. 2 Radiant Intensity vs Forward Current gra_028.ds4

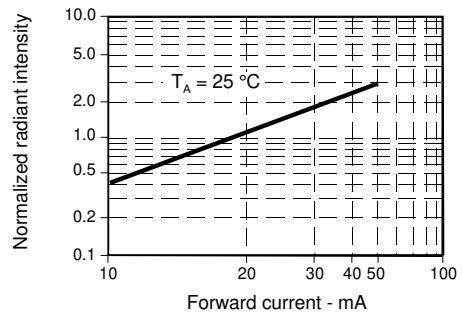


Fig. 3 Forward Voltage vs Forward Current gra_003.ds4

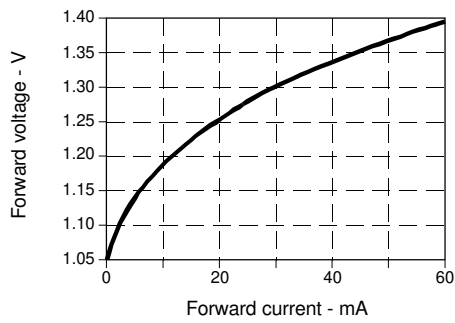


Fig. 4 Forward Voltage vs Temperature gra_207.ds4

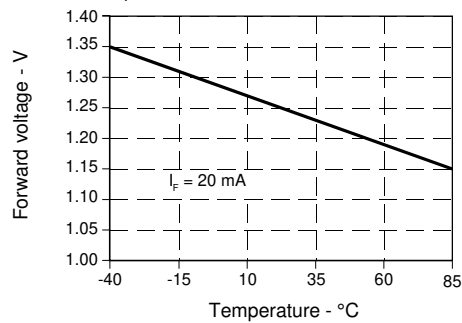


Fig. 5 Spectral Bandwidth gra_005.ds4

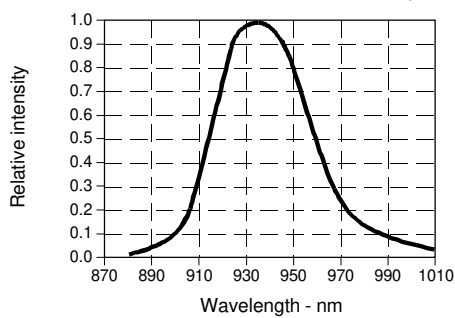
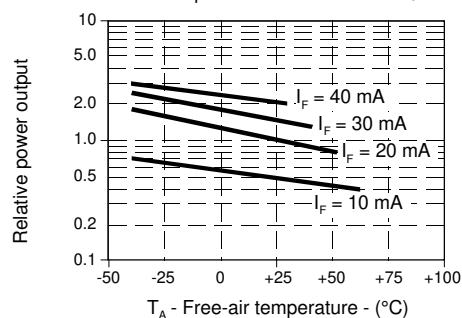


Fig. 6 Relative Power Output vs Free Air Temperature gra_130.ds4



All Performance Curves Show Typical Values

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